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**Abstract of the Disclosure**

A method for forming a trench capacitor. The method includes forming a trench in a semiconductor substrate. A conformal layer of semiconductor material is deposited in the trench. The surface of the conformal layer of semiconductor material is roughened.

- 5 An insulator layer is formed outwardly from the roughened, conformal layer of semiconductor material. A polycrystalline semiconductor plate is formed outwardly from the insulator layer in the trench.

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